

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

Listing of the Claims:

1 – 6. (Cancelled)

7. (Previously Presented) A field effect transistor, comprising:
a substrate having a recess in a surface thereof, the recess having a curvilinear shape;
a gate dielectric layer disposed superjacent the curvilinear recess and superjacent a portion of a top surface of the substrate;
a gate electrode completely overlying the gate dielectric layer; and
source/drain terminals disposed in the substrate in alignment with a pair of laterally opposed gate electrode sidewalls; and
wherein the source/drain terminals comprise an extension which extends to a more shallow depth within the substrate than the source/drain terminals to which it corresponds and extends downwardly, from approximately the surface of the substrate, along the curvilinear sides of the recess, a portion of the gate dielectric layer overlaying an inner-most portion of the extension.

8. (Previously Presented) The transistor of Claim 7, wherein the gate electrode conforms to a recessed channel.

9. (Previously Presented) The transistor of Claim 7, wherein the gate electrode conforms to a recessed channel.